



Continental Device India Limited

An ISO/TS 16949, ISO 9001 and ISO 14001 Certified Company

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ISO 14001



SOT-23 Formed SMD Package

CMBTA92

CMBTA93

SILICON EPITAXIAL TRANSISTORS

P-N-P transistor

Marking

CMBTA92 = 2D

CMBTA93 = 2E

PACKAGE OUTLINE DETAILS

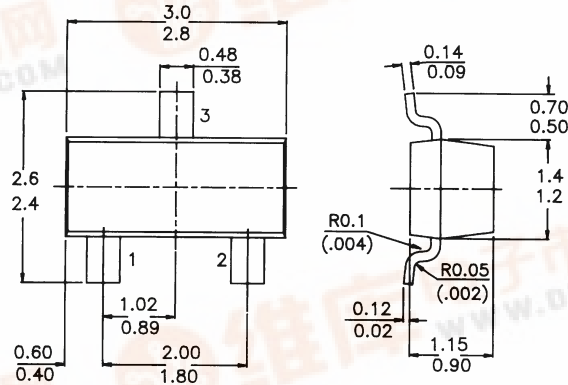
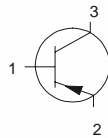
ALL DIMENSIONS IN mm

Pin configuration

1 = BASE

2 = EMITTER

3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Emitter-base voltage (open collector)

Collector current (d.c.)

Total power dissipation up to $T_{amb} = 25^{\circ}\text{C}$

D.C. current gain

$-I_C = 10\text{ mA}$; $-V_{CE} = 10\text{ V}$

Transition frequency at $f = 100\text{ MHz}$

$-I_C = 10\text{ mA}$; $-V_{CE} = 20\text{ V}$

Collector-base capacitance at $f = 1\text{ MHz}$

$I_E = 0$; $-V_{CB} = 20\text{ V}$

CMBTA92

A93

| | | |
|-----------------|-----|-------|
| $-V_{CBO}$ max. | 300 | 200 V |
| $-V_{CEO}$ max. | 300 | 200 V |
| $-V_{EBO}$ max. | 5 | V |
| $-I_C$ max. | 500 | mA |
| P_{tot} | 250 | mW |
| h_{FE} min. | 40 | |
| f_T min. | 50 | MHz |
| C_{cb} max. | 6 | 8 pF |



CMBTA92
CMBTA93

RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting values

| | | CMBTA92 | A93 |
|--|------------|------------------------------|------------------|
| Collector-base voltage (open emitter) | $-V_{CBO}$ | max. 300 | 200 V |
| Collector-emitter voltage (open base) | $-V_{CEO}$ | max. 300 | 200 V |
| Emitter-base voltage (open collector) | $-V_{EBO}$ | max. 5 | V |
| Collector current (d.c.) | $-I_C$ | max. 500 | mA |
| Total power dissipation up to $T_{amb} = 25^\circ\text{C}$ | P_{tot} | max. 250 | mW |
| Storage temperature | T_{stg} | -55 to +150 $^\circ\text{C}$ | |
| Junction temperature | T_j | max. 150 | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

$$T_j = P (R_{th\ j-t} + R_{th\ t-s} + R_{th\ s-a}) + T_{amb}$$

Thermal resistance

| | | | |
|--------------------------|---------------|-----|-----|
| from junction to ambient | $R_{th\ j-a}$ | 500 | K/W |
|--------------------------|---------------|-----|-----|

CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Collector-emitter breakdown voltage

| | | | |
|-------------------------------|----------------------|-----|-------|
| $-I_C = 1\text{ mA}; I_B = 0$ | $-V_{(BR)CEO\ min.}$ | 300 | 200 V |
|-------------------------------|----------------------|-----|-------|

Collector-base breakdown voltage

| | | | |
|------------------------------------|----------------------|-----|-------|
| $-I_C = 100\ \mu\text{A}; I_E = 0$ | $-V_{(BR)CBO\ min.}$ | 300 | 200 V |
|------------------------------------|----------------------|-----|-------|

Collector cut-off current

| | | | |
|-----------------------------------|------------|-----------|--------------------|
| $-V_{CB} = 200\text{ V}; I_E = 0$ | $-I_{CBO}$ | max. 0.25 | μA |
| $-V_{CB} = 160\text{ V}; I_E = 0$ | $-I_{CBO}$ | max. - | 0.25 μA |

Emitter-base breakdown voltage

| | | | |
|------------------------------------|----------------------|---|---|
| $-I_E = 100\ \mu\text{A}; I_C = 0$ | $-V_{(BR)EBO\ min.}$ | 5 | V |
|------------------------------------|----------------------|---|---|

Emitter cut-off current

| | | | |
|----------------------------------|------------|----------|--------|
| $I_C = 0; -V_{BE} = 3\text{ V};$ | $-I_{EBO}$ | max. 0.1 | 0.1 mA |
|----------------------------------|------------|----------|--------|

Collector-base capacitance at $f = 1\text{ MHz}$

| | | | |
|----------------------------------|----------|--------|------|
| $I_E = 0; -V_{CB} = 20\text{ V}$ | C_{cb} | max. 6 | 8 pF |
|----------------------------------|----------|--------|------|

Saturation voltages

| | | | |
|---|--------------|----------|-------|
| $-I_C = 20\text{ mA}; -I_B = 2\text{ mA}$ | $-V_{CEsat}$ | max. 0.5 | 0.5 V |
| $-I_C = 20\text{ mA}; -I_B = 2\text{ mA}$ | $-V_{BEsat}$ | max. 0.9 | 0.9 V |

D.C. current gain

| | | | |
|--|----------|---------|--|
| $-I_C = 1\text{ mA}; -V_{CE} = 10\text{ V}$ | h_{FE} | min. 25 | |
| $-I_C = 10\text{ mA}; -V_{CE} = 10\text{ V}$ | h_{FE} | min. 40 | |
| $-I_C = 30\text{ mA}; -V_{CE} = 10\text{ V}$ | h_{FE} | min. 25 | |

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/ CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-2579 6150, 5141 1112 Fax +q 91-11-2579 5290, 5141 1119
email@cdil.com www.cdilsemi.com